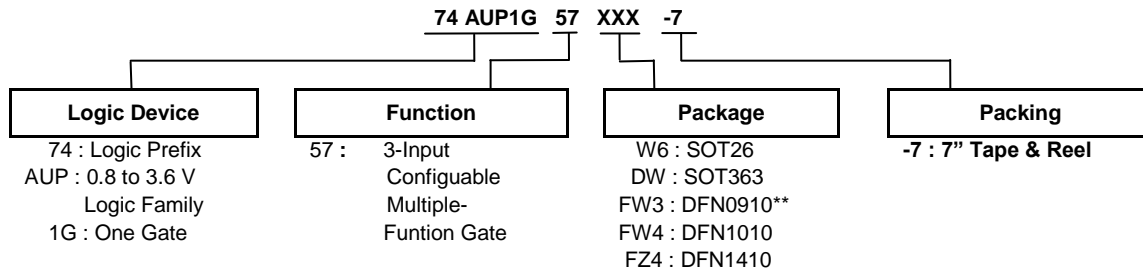


Ordering Information



Device	Package Code	Package (Notes 4 & 5)	Package Size	7" Tape and Reel	
				Quantity	Part Number Suffix
74AUP1G57W6-7	W6	SOT26	3.0mm x 2.8mm x 1.2mm 0.95 mm lead pitch	3,000/Tape & Reel	-7
74AUP1G57DW-7	DW	SOT363	2.0mm x 2.0mm x 1.1mm 0.65 mm lead pitch	3,000/Tape & Reel	-7
74AUP1G57FW3-7**	FW3	X2-DFN0910-6	0.9mm x 1.0mm x 0.35mm 0.3 mm lead pitch	5,000/Tape & Reel	-7
74AUP1G57FW4-7	FW4	X2-DFN1010-6	1.0mm x 1.0mm x 0.4mm 0.35 mm lead pitch	5,000/Tape & Reel	-7
74AUP1G57FZ4-7	FZ4	X2-DFN1410-6	1.4mm x 1.0mm x 0.4mm 0.5 mm lead pitch	5,000/Tape & Reel	-7

Notes: 4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
5. The taping orientation is located on our website at <http://www.diodes.com/datasheets/ap02007.pdf>.
** The X2-DFN0910-6 is a future product.

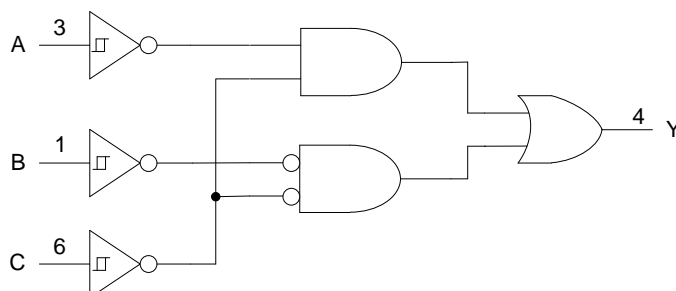
Pin Descriptions

Pin Name	Function
B	Data Input
GND	Ground
A	Data Input
Y	Data Output
V _{CC}	Supply Voltage
C	Data Input

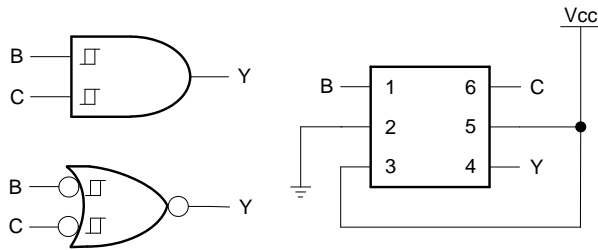
Function Table

Inputs			Output
C	B	A	Y
L	L	L	H
L	L	H	L
L	H	L	H
L	H	H	L
H	L	L	L
H	L	H	L
H	H	L	H
H	H	H	H

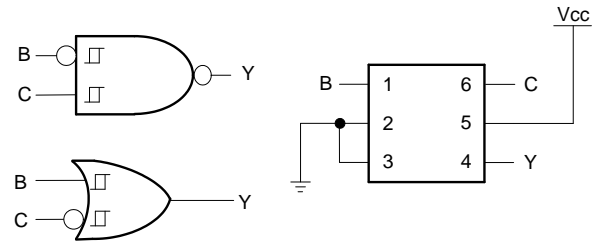
Logic Diagram



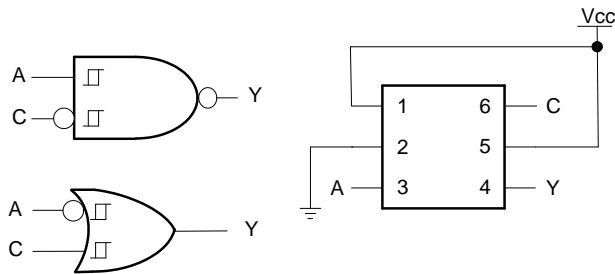
Logic Configurations



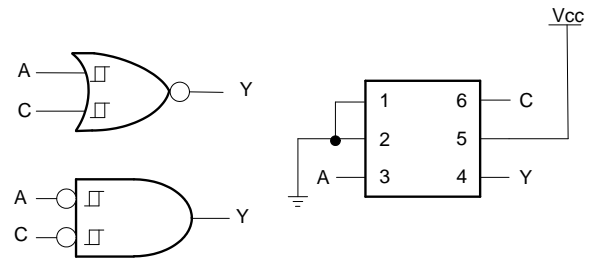
Configuration 1
2-Input AND Gate
2-Input NOR Gate with Both Inputs Inverted



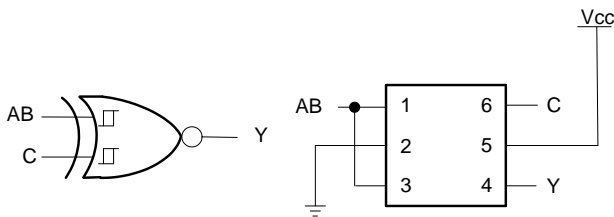
Configuration 2
2-Input NAND Gate with B Input Inverted
2-Input OR Gate with C input Inverted



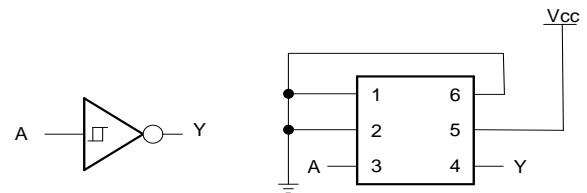
Configuration 3
2-Input NAND Gate with C Input Inverted
2-Input OR Gate with A Input Inverted



Configuration 4
2-Input NOR Gate
2-Input AND Gate with Both Inputs Inverted



Configuration 5
2-Input XNOR Gate



Configuration 6
Inverter

Function Selection Table	
Logic Function	Configuration
2-Input AND	1
2-Input AND with both inputs inverted	4
2-Input NAND with inverted input	2, 3
2-Input OR with inverted input	2, 3
2-Input NOR	4
2-Input NOR with both inputs inverted	1
2-Input XNOR	5
1-Input INVERTER	6

Absolute Maximum Ratings (Notes 6 & 7)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to +4.6	V
V _I	Input Voltage Range	-0.5 to +4.6	V
V _O	Voltage applied to output in high or low state	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current V _I < 0	-50	mA
I _{OK}	Output Clamp Current (V _O < 0)	-50	mA
I _O	Continuous Output Current (V _O = 0 to V _{CC})	±20	mA
I _{CC}	Continuous Current through V _{CC}	50	mA
I _{GND}	Continuous Current through GND	-50	mA
T _J	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Notes: 6. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.
7. Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.

Recommended Operating Conditions (Note 8)

Symbol	Parameter		Min	Max	Unit
V _{CC}	Operating Voltage	-	0.8	3.6	V
V _I	Input Voltage	-	0	3.6	V
V _O	Output Voltage	Active Mode	0	V _{CC}	V
		Power Down Mode	0	3.6	V
I _{OH}	High-Level Output Current	V _{CC} = 0.8 V	-	-20	μA
		V _{CC} = 1.1 V	-	-1.1	mA
		V _{CC} = 1.4 V	-	-1.7	
		V _{CC} = 1.65 V	-	-1.9	
		V _{CC} = 2.3 V	-	-3.1	
		V _{CC} = 3.0 V	-	-4	
I _{OL}	Low-Level Output Current	V _{CC} = 0.8 V	-	20	uA
		V _{CC} = 1.1 V	-	1.1	mA
		V _{CC} = 1.4 V	-	1.7	
		V _{CC} = 1.65 V	-	1.9	
		V _{CC} = 2.3 V	-	3.1	
		V _{CC} = 3.0 V	-	4	
T _A	Operating Free-Air Temperature	-	-40	+125	°C

Note: 8. Unused inputs should be held at V_{CC} or Ground.

Electrical Characteristics

Symbol	Parameter	Test Conditions	Vcc	T _A = +25°C		T _A = -40 to +85°C		Unit
				Min	Max	Min	Max	
V _{T+}	Positive-Going Input Threshold Voltage	-	0.8V	0.3	0.65	0.3	0.7	V
		-	1.1V	0.53	0.9	0.53	0.9	
		-	1.4V	0.74	1.11	0.74	1.11	
		-	1.65V	0.91	1.29	0.91	1.29	
		-	2.3V	1.37	1.77	1.37	1.77	
		-	3.0V	1.88	2.29	1.88	2.29	
V _{T-}	Negative-Going Input Threshold Voltage	-	0.8V	0.1	0.6	0.1	0.6	V
		-	1.1V	0.26	0.65	0.26	0.65	
		-	1.4V	0.39	0.75	0.39	0.75	
		-	1.65V	0.47	0.84	0.47	0.84	
		-	2.3V	0.69	1.04	0.69	1.04	
		-	3.0V	0.88	1.24	0.88	1.24	
ΔV _T	Hysteresis (V _{T+} - V _{T-})	-	0.8V	0.07	0.5	0.07	0.5	V
		-	1.1V	0.08	0.46	0.08	0.46	
		-	1.4V	0.18	0.56	0.18	0.56	
		-	1.65V	0.27	0.66	0.27	0.66	
		-	2.3V	0.53	0.92	0.53	0.92	
		-	3.0V	0.79	1.31	0.79	1.31	
V _{OH}	High-Level Output Voltage	I _{OH} = -20μA	0.8V to 3.6V	V _{CC} - 0.1	-	V _{CC} - 0.1	-	V
		I _{OH} = -1.1mA	1.1V	0.75 x V _{CC}	-	0.7 x V _{CC}	-	
		I _{OH} = -1.7mA	1.4V	1.11	-	1.03	-	
		I _{OH} = -1.9mA	1.65V	1.32	-	1.3	-	
		I _{OH} = -2.3mA	2.3V	2.05	-	1.97	-	
		I _{OH} = -3.1mA		1.9	-	1.85	-	
		I _{OH} = -2.7mA	3V	2.72	-	2.67	-	
		I _{OH} = -4mA		2.6	-	2.55	-	
V _{OL}	Low-Level Input Voltage	I _{OL} = 20μA	0.8V to 3.6V	-	0.1	-	0.1	V
		I _{OL} = 1.1mA	1.1V	-	0.3 x V _{CC}	-	0.3 x V _{CC}	
		I _{OL} = 1.7mA	1.4V	-	0.31	-	0.37	
		I _{OL} = 1.9mA	1.65 V	-	0.31	-	0.35	
		I _{OL} = 2.3mA	2.3V	-	0.31	-	0.33	
		I _{OL} = 3.1mA		-	0.44	-	0.45	
		I _{OL} = 2.7mA	3V	-	0.31	-	0.33	
		I _{OL} = 4mA		-	0.44	-	0.45	
I _I	Input Current	A or B Input V _I = GND to 3.6 V	0V to 3.6V	-	± 0.1	-	± 0.5	μA
I _{OFF}	Power Down Leakage Current	V _I or V _O = 0V to 3.6V	0	-	± 0.2	-	± 0.6	μA
ΔI _{OFF}	Delta Power Down Leakage Current	V _I or V _O = 0V to 3.6V	0V to 0.2 V	-	± 0.2	-	± 0.6	μA
I _{CC}	Supply Current	V _I = GND or V _{CC} I _O = 0	0.8V to 3.6V	-	0.5	-	0.9	μA
ΔI _{CC}	Additional Supply Current	One input at V _{CC} - 0.6 V Other inputs at V _{CC} or GND	3.3V	-	40	-	50	μA

Electrical Characteristics (continued)

Symbol	Parameter	Test Conditions	Vcc	T _A = -40 to +125°C		Unit
				Min	Max	
V _{T+}	Positive-Going Input Threshold Voltage	-	0.8V	0.3	0.7	V
		-	1.1V	0.53	0.92	
		-	1.4V	0.74	1.13	
		-	1.65V	0.91	1.31	
		-	2.3V	1.37	1.8	
		-	3.0V	1.88	2.32	
V _{T-}	Negative-Going Input Threshold Voltage	-	0.8V	0.1	0.6	V
		-	1.1V	0.26	0.65	
		-	1.4V	0.39	0.75	
		-	1.65V	0.47	0.84	
		-	2.3V	0.69	1.04	
		-	3.0V	0.88	1.24	
ΔV _T	Hysteresis (V _{T+} - V _{T-})	-	0.8V	0.07	0.5	V
		-	1.1V	0.08	0.46	
		-	1.4V	0.18	0.56	
		-	1.65V	0.27	0.66	
		-	2.3V	0.53	0.92	
		-	3.0V	0.79	1.31	
V _{OH}	High-Level Output Voltage	I _{OH} = -20μA	0.8V to 3.6V	V _{CC} - 0.11	-	V
		I _{OH} = -1.1mA	1.1V	0.6 x V _{CC}	-	
		I _{OH} = -1.7mA	1.4V	0.93	-	
		I _{OH} = -1.9mA	1.65V	1.17	-	
		I _{OH} = -2.3mA	2.3V	1.77	-	
		I _{OH} = -3.1mA		1.67	-	
		I _{OH} = -2.7mA	3V	2.40	-	
		I _{OH} = -4mA		2.30	-	
V _{OL}	Low-Level Input Voltage	I _{OL} = 20μA	0.8V to 3.6V	-	0.11	V
		I _{OL} = 1.1mA	1.1V	-	0.33 x V _{CC}	
		I _{OL} = 1.7mA	1.4V	-	0.41	
		I _{OL} = 1.9mA	1.65 V	-	0.39	
		I _{OL} = 2.3mA	2.3V	-	0.36	
		I _{OL} = 3.1mA		-	0.50	
		I _{OL} = 2.7mA	3V	-	0.36	
		I _{OL} = 4mA		-	0.50	
I _I	Input Current	A or B Input V _I = GND to 3.6 V	0V to 3.6V	-	± 0.75	μA
I _{OFF}	Power Down Leakage Current	V _I or V _O = 0V to 3.6V	0	-	± 1.0	μA
ΔI _{OFF}	Delta Power Down Leakage Current	V _I or V _O = 0V to 3.6V	0V to 0.2 V	-	± 2.5	μA
I _{CC}	Supply Current	V _I = GND or V _{CC} I _O = 0	0.8V to 3.6V	-	1.4	μA
ΔI _{CC}	Additional Supply Current	One input at V _{CC} - 0.6 V Other inputs at V _{CC} or GND	3.3V	-	75	μA

Package Characteristics

Symbol	Parameter	Package	Test Conditions	Min	Typ.	Max	Unit
θ_{JA}	Thermal Resistance Junction-to-Ambient	SOT26	(Note 9)	-	166	-	°C/W
		SOT363		-	371	-	
		X2-DFN0910-6		-	450	-	
		X2-DFN1010-6		-	445	-	
		X2-DFN1410-6		-	430	-	
θ_{JC}	Thermal Resistance Junction-to-Case	SOT26	(Note 9)	-	46	-	°C/W
		SOT363		-	143	-	
		X2-DFN0910-6		-	255	-	
		X2-DFN1010-6		-	250	-	
		X2-DFN1410-6		-	190	-	

Note: 9. Test condition for each of the 8 package types: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Operating Characteristics (@T_A = +25°C, unless otherwise specified.)

Parameter		Test Conditions	V _{CC}	TYP	Unit
C _{pd}	Power Dissipation Capacitance	f = 1MHz No Load	0.8 V	4	pF
			1.2 V ± 0.1 V	4	
			1.5 V ± 0.1 V	4	
			1.8 V ± 0.15 V	4	
			2.5 V ± 0.2 V	4.4	
			3.3 ± 0.3 V	4.8	
C _i	Input Capacitance	V _i = V _{CC} or GND	0 V or 3.3 V	1.1	pF
C _o	Output Capacitance	V ₀ = V _{CC} or GND	0 V	2.0	pF

Switching Characteristics

C_L = 5pF, See Figure 1

Parameter	From Input	TO OUTPUT	V _{CC}	T _A = +25°C			T _A = -40°C to +85°C		T _A = -40°C to +125°C		Unit
				Min	TYP	Max	Min	Max	Min	Max	
t _{pd}	A, B, or C	Y	0.8 V	-	28	-	-	-	-	-	ns
			1.2 V ± 0.1 V	2.6	7.4	14.4	2.1	14.8	2.1	15.1	
			1.5 V ± 0.1 V	1.9	4.6	7.6	1.4	8.2	1.4	8.6	
			1.8 V ± 0.15 V	1.4	3.9	6.2	0.9	6.8	0.9	7.2	
			2.5 V ± 0.2 V	1.1	3.1	4.5	0.6	5.1	0.6	5.3	
			3.3 V ± 0.3 V	1	2.8	3.9	0.5	4.1	0.5	4.3	

Switching Characteristics (continued)

 $C_L=10\text{pF}$, See Figure 1

Parameter	From Input	TO OUTPUT	V_{CC}	$T_A = +25^\circ\text{C}$			$T_A = -40^\circ\text{C to } +85^\circ\text{C}$		$T_A = -40^\circ\text{C to } +125^\circ\text{C}$		Unit
				Min	TYP	Max	Min	Max	Min	Max	
t_{pd}	A, B, or C	Y	0.8 V	-	32	-	-	-	-	-	ns
			$1.2\text{ V} \pm 0.1\text{ V}$	2.6	8.3	16.4	2.1	17	2.1	17.3	
			$1.5\text{ V} \pm 0.1\text{ V}$	1.9	5.2	8.7	1.4	9.4	1.4	9.8	
			$1.8\text{ V} \pm 0.15\text{ V}$	1.4	4.5	7	0.9	7.8	0.9	8.2	
			$2.5\text{ V} \pm 0.2\text{ V}$	1.1	3.7	5.2	0.6	5.9	0.6	6.2	
			$3.3\text{ V} \pm 0.3\text{ V}$	1	3.4	4.6	0.5	4.9	0.5	5.1	

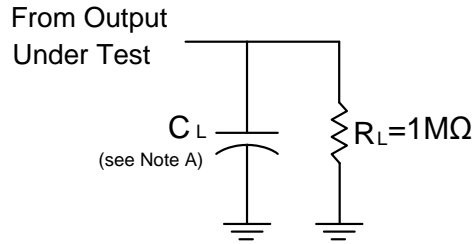
 $C_L=15\text{pF}$, See Figure 1

Parameter	From Input	TO OUTPUT	V_{CC}	$T_A = +25^\circ\text{C}$			$T_A = -40^\circ\text{C to } +85^\circ\text{C}$		$T_A = -40^\circ\text{C to } +125^\circ\text{C}$		Unit
				Min	TYP	Max	Min	Max	Min	Max	
t_{pd}	A, B, or C	Y	0.8 V	-	38	-	-	-	-	-	ns
			$1.2\text{ V} \pm 0.1\text{ V}$	3.4	9.1	17.9	3.1	19.8	3.1	20	
			$1.5\text{ V} \pm 0.1\text{ V}$	2.8	5.7	9.6	2.3	10.4	2.3	10.9	
			$1.8\text{ V} \pm 0.15\text{ V}$	2.1	4.9	7.8	1.6	8.7	1.6	9.2	
			$2.5\text{ V} \pm 0.2\text{ V}$	1.7	4.1	5.8	1.2	6.5	1.2	6.9	
			$3.3\text{ V} \pm 0.3\text{ V}$	1.5	3.8	5.1	1	5.5	1	5.7	

 $C_L=30\text{pF}$, See Figure 1

Parameter	From Input	TO OUTPUT	V_{CC}	$T_A = +25^\circ\text{C}$			$T_A = -40^\circ\text{C to } +85^\circ\text{C}$		$T_A = -40^\circ\text{C to } +125^\circ\text{C}$		Unit
				Min	TYP	Max	Min	Max	Min	Max	
t_{pd}	A, B, or C	Y	0.8 V	-	46	-	-	-	-	-	ns
			$1.2\text{ V} \pm 0.1\text{ V}$	4.6	11.9	23.8	3.9	24.9	3.9	25.4	
			$1.5\text{ V} \pm 0.1\text{ V}$	3.6	7.4	12.2	3.4	13.3	3.4	14.1	
			$1.8\text{ V} \pm 0.15\text{ V}$	3.1	6.2	9.9	2.6	11.1	2.6	11.8	
			$2.5\text{ V} \pm 0.2\text{ V}$	2.6	5.2	7.4	2.1	8.3	2.1	8.8	
			$3.3\text{ V} \pm 0.3\text{ V}$	2.3	4.9	6.6	1.8	7	1	7.4	

Parameter Measurement Information



V_{CC}	Inputs		V_M	C_L
	V_I	t_r/t_f		
0.8 V	V_{CC}	$\leq 3ns$	$V_{CC}/2$	5, 10, 15, 30 pF
1.2V±0.1V	V_{CC}	$\leq 3ns$	$V_{CC}/2$	5, 10, 15, 30 pF
1.5V±0.1V	V_{CC}	$\leq 3ns$	$V_{CC}/2$	5, 10, 15, 30 pF
1.8V±0.15V	V_{CC}	$\leq 3ns$	$V_{CC}/2$	5, 10, 15, 30 pF
2.5V±0.2V	V_{CC}	$\leq 3ns$	$V_{CC}/2$	5, 10, 15, 30 pF
3.3V±0.3V	V_{CC}	$\leq 3ns$	$V_{CC}/2$	5, 10, 15, 30 pF

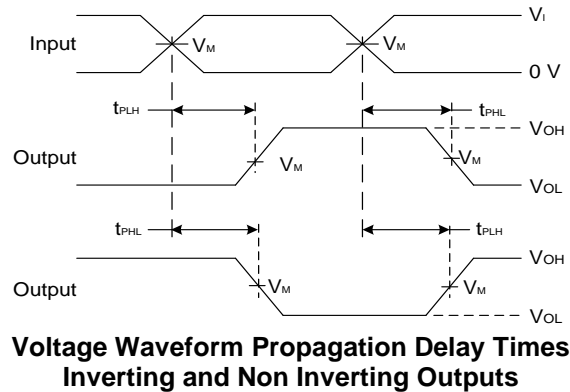
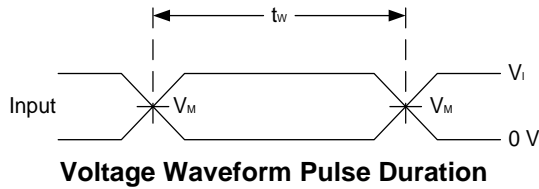
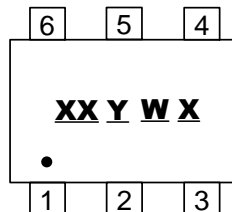


Figure 1. Load Circuit and Voltage Waveforms

- Notes:
- A. Includes test lead and test apparatus capacitance.
 - B. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
 - C. Inputs are measured separately one transition per measurement.
 - D. t_{PLH} and t_{PHL} are the same as t_{PD} .

Marking Information

(1) SOT26, SOT363

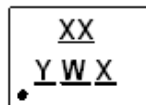


XX : Identification code
Y : Year 0~9
W : Week : A~Z : 1~26 week;
a~z : 27~52 week; z represents
52 and 53 week
X : A~Z : Internal Code

Part Number	Package	Identification Code
74AUP1G57W6	SOT26	AP
74AUP1G57DW	SOT363	BV

(2) X2-DFN0910-6, X2-DFN1010-6, X2-DFN1410-6

(Top View)

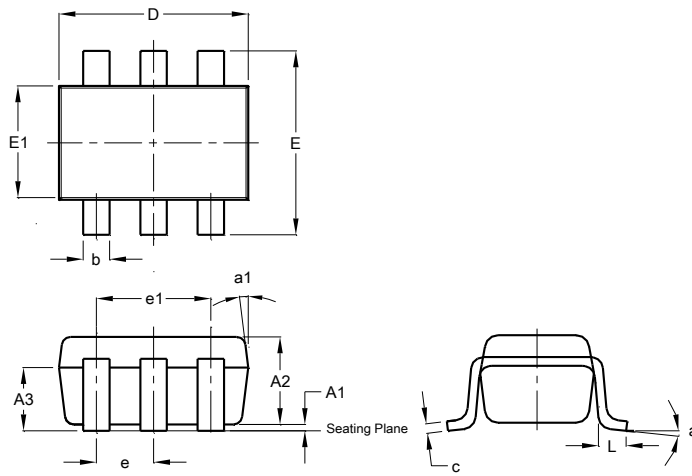


XX : Identification Code
Y : Year : 0~9
W : Week : A~Z : 1~26 week;
a~z : 27~52 week; z represents
52 and 53 week
X : A~Z : Internal code

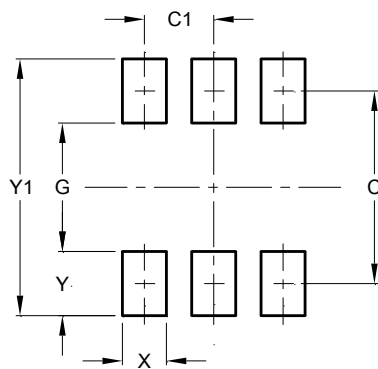
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74AUP1G57FW4	X2-DFN1010-6	BV
74AUP1G57FZ4	X2-DFN1410-6	NG

SOT26 Package Outline Dimensions and Suggested Pad Layout

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



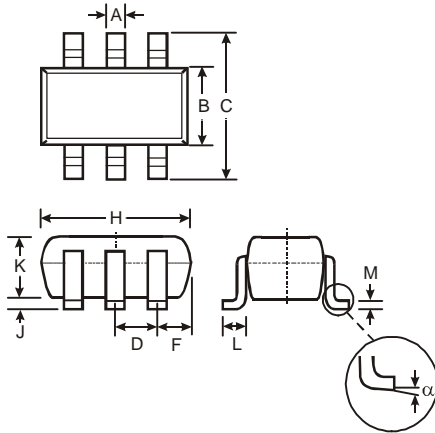
SOT26			
Dim	Min	Max	Typ
A1	0.013	0.10	0.05
A2	1.00	1.30	1.10
A3	0.70	0.80	0.75
b	0.35	0.50	0.38
c	0.10	0.20	0.15
D	2.90	3.10	3.00
e	-	-	0.95
e1	-	-	1.90
E	2.70	3.00	2.80
E1	1.50	1.70	1.60
L	0.35	0.55	0.40
a	-	-	8°
a1	-	-	7°
All Dimensions in mm			



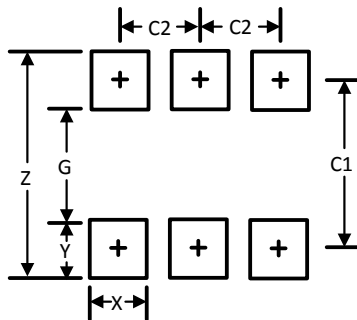
Dimensions	Value (in mm)
C	2.40
C1	0.95
G	1.60
X	0.55
Y	0.80
Y1	3.20

SOT363 Package Outline Dimensions and Suggested Pad Layout

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



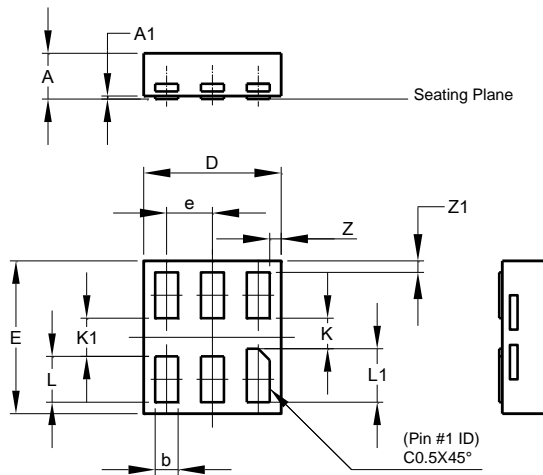
SOT363			
Dim	Min	Max	Typ
A	0.10	0.30	0.25
B	1.15	1.35	1.30
C	2.00	2.20	2.10
D	0.65 Typ		
F	0.40	0.45	0.425
H	1.80	2.20	2.15
J	0	0.10	0.05
K	0.90	1.00	1.00
L	0.25	0.40	0.30
M	0.10	0.22	0.11
α	0°	8°	-
All Dimensions in mm			



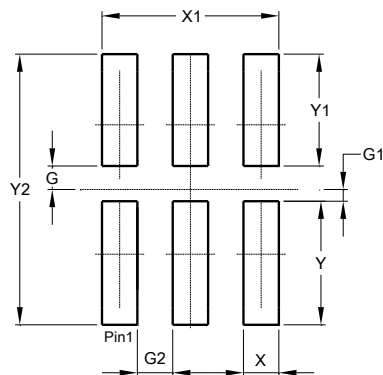
Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C1	1.9
C2	0.65

X2-DFN0910-6 Package Outline Dimensions and Suggested Pad Layout

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



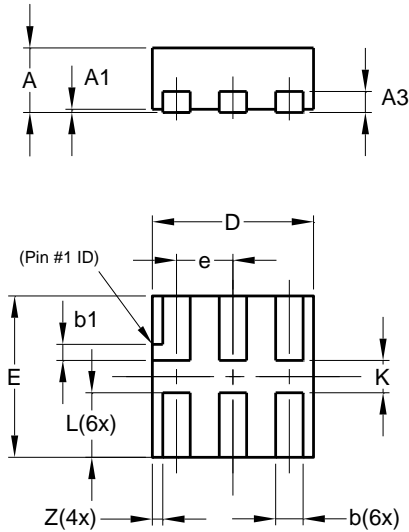
X2-DFN0910-6			
Dim	Min	Max	Typ
A	-	0.35	0.30
A1	0	0.03	0.02
b	0.10	0.20	0.15
D	0.85	0.95	0.90
E	0.95	1.05	1.00
e	-	-	0.30
K	0.20	-	-
K1	0.25	-	-
L	0.25	0.35	0.30
L1	0.30	0.40	0.35
Z	-	-	0.075
Z1	-	-	0.075
All Dimensions in mm			



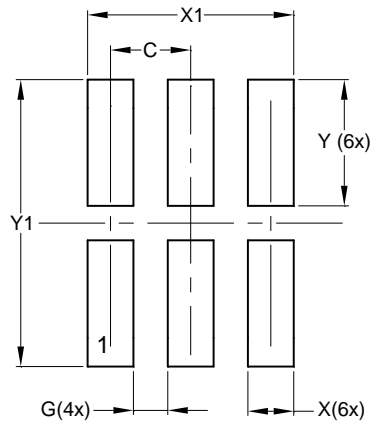
Dimensions	Value (in mm)
G	0.100
G1	0.050
G2	0.150
X	0.150
X1	0.750
Y	0.525
Y1	0.475
Y2	1.150

X2-DFN1010-6 Package Outline Dimensions and Suggested Pad Layout

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



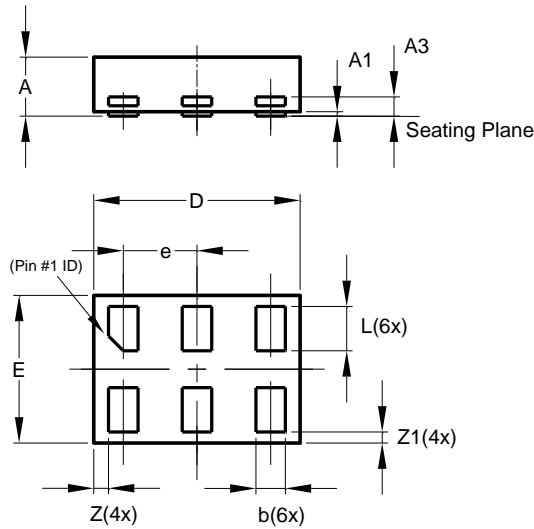
X2-DFN1010-6			
Dim	Min	Max	Typ
A	—	0.40	0.39
A1	0.00	0.05	0.02
A3	—	—	0.13
b	0.14	0.20	0.17
b1	0.05	0.15	0.10
D	0.95	1.05	1.00
E	0.95	1.05	1.00
e	—	—	0.35
L	0.35	0.45	0.40
K	0.15	—	—
Z	—	—	0.065
All Dimensions in mm			



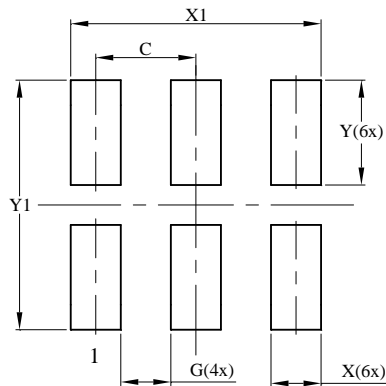
Dimensions	Value (in mm)
C	0.350
G	0.150
X	0.200
X1	0.900
Y	0.550
Y1	1.250

X2-DFN1410-6 Package Outline Dimensions and Suggested Pad Layout

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



X2-DFN1410-6			
Dim	Min	Max	Typ
A	—	0.40	0.39
A1	0.00	0.05	0.02
A3	—	—	0.13
b	0.15	0.25	0.20
D	1.35	1.45	1.40
E	0.95	1.05	1.00
e	—	—	0.50
L	0.25	0.35	0.30
Z	—	—	0.10
Z1	0.045	0.105	0.075
All Dimensions in mm			



Dimensions	Value (in mm)
C	0.500
G	0.250
X	0.250
X1	1.250
Y	0.525
Y1	1.250

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